Rafael Garcia

List of Publications by Year
in descending order

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183	2,530	279487	264894
papers	citations	23 h-index	42 g-index

187	187	187	2357
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Application of advanced (S)TEM methods for the study of nanostructured porous functional surfaces: A few working examples. Materials Characterization, 2022, 185, 111741.	1.9	5
2	Anisotropic optical properties of indium tin oxide thin films prepared by ion beam sputtering under oblique angle deposition. Applied Surface Science, 2022, 595, 152945.	3.1	6
3	Controlled grain-size thermochromic VO2 coatings by the fast oxidation of sputtered vanadium or vanadium oxide films deposited at glancing angles. Surfaces and Interfaces, 2021, 27, 101581.	1.5	6
4	Simultaneous Optical and Electrical Characterization of GaN Nanowire Arrays by Means of Vis-IR Spectroscopic Ellipsometry. Journal of Physical Chemistry C, 2020, 124, 1535-1543.	1.5	5
5	Optical and nanostructural insights of oblique angle deposited layers applied for photonic coatings. Applied Surface Science, 2020, 520, 146312.	3.1	7
6	On the importance of light scattering for high performances nanostructured antireflective surfaces. Acta Materialia, 2020, 188, 386-393.	3.8	5
7	Surface oxidation of amorphous Si and Ge slanted columnar and mesoporous thin films: Evidence, scrutiny and limitations for infrared optics. Applied Surface Science, 2019, 493, 807-817.	3.1	8
8	Nanostructure and Physical Properties Control of Indium Tin Oxide Films Prepared at Room Temperature through Ion Beam Sputtering Deposition at Oblique Angles. Journal of Physical Chemistry C, 2019, 123, 14036-14046.	1.5	12
9	Unravelling the polarity of InN quantum dots using a modified approach of negative-spherical-aberration imaging. Nanoscale, 2019, 11, 13632-13638.	2.8	9
10	Porosity Control for Plasma-Assisted Molecular Beam Epitaxy of GaN Nanowires. Crystal Growth and Design, 2019, 19, 2461-2469.	1.4	7
11	(S)TEM methods contributions to improve the fabrication of InGaN thin films on Si, and InN nanostructures on flat Si and rough InGaN. Journal of Alloys and Compounds, 2019, 783, 697-708.	2.8	5
12	Towards perfect MWIR transparency using oblique angle deposition. Applied Surface Science, 2019, 470, 943-950.	3.1	9
13	Comprehensive (S)TEM characterization of polycrystalline GaN/AlN layers grown on LTCC substrates. Ceramics International, 2019, 45, 9114-9125.	2.3	10
14	Formation mechanisms of single-crystalline InN quantum dots fabricated via droplet epitaxy. Journal of Crystal Growth, 2018, 493, 65-75.	0.7	5
15	Engineering of III-Nitride Semiconductors on Low Temperature Co-fired Ceramics. Scientific Reports, 2018, 8, 6879.	1.6	6
16	Low temperature epitaxial deposition of GaN on LTCC substrates. , 2017, , .		1
17	Direct Measurement of Polarization-Induced Fields in GaN/AlN by Nano-Beam Electron Diffraction. Scientific Reports, 2016, 6, 28459.	1.6	25
18	Inline electron holography and VEELS for the measurement of strain in ternary and quaternary (In,Al,Ga)N alloyed thin films and its effect on bandgap energy. Journal of Microscopy, 2016, 261, 27-35.	0.8	3

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19	Development of a magneto-optical sensor prototype to measure current by means of the induced magnetic field. Sensors and Actuators A: Physical, 2016, 249, 231-241.	2.0	7
20	Quantitative Chemical Mapping of InGaN Quantum Wells from Calibrated High-Angle Annular Dark Field Micrographs. Microscopy and Microanalysis, 2015, 21, 994-1005.	0.2	3
21	Analysis of the stability of InGaN/GaN multiquantum wells against ion beam intermixing. Nanotechnology, 2015, 26, 425703.	1.3	6
22	The Role of Edge Dislocations on the Red Luminescence of ZnO Films Deposited by RF-Sputtering. Journal of Nanomaterials, 2015, 2015, 1-11.	1.5	3
23	Improving Magnetooptical Faraday Effect of maghemite/silica nanocomposites. Materials Chemistry and Physics, 2015, 154, 1-9.	2.0	9
24	Near-infrared emitting In-rich InGaN layers grown directly on Si: Towards the whole composition range. Applied Physics Letters, 2015, 106, .	1.5	43
25	Stranski-Krastanov InN/InGaN quantum dots grown directly on Si(111). Applied Physics Letters, 2015, 106, .	1.5	21
26	Epitaxial growth of Fe islands on LaAlO3 (001) substrates. Journal of Crystal Growth, 2014, 391, 121-129.	0.7	0
27	Selective ion-induced intermixing and damage in low-dimensional GaN/AlN quantum structures. Nanotechnology, 2013, 24, 505717.	1.3	14
28	Evaluation of interpolations of InN, AlN and GaN lattice and elastic constants for their ternary and quaternary alloys. Journal Physics D: Applied Physics, 2013, 46, 245502.	1.3	19
29	Spontaneous formation of InGaN nanowall network directly on Si. Applied Physics Letters, 2013, 102, .	1.5	12
30	Uniform Low-to-High In Composition InGaN Layers Grown on Si. Applied Physics Express, 2013, 6, 115503.	1.1	14
31	Structural and optical characterization of Mg-doped GaAs nanowires grown on GaAs and Si substrates. Journal of Applied Physics, 2013, 114, .	1.1	25
32	N-type conductivity and properties of carbon-doped InN(0001) films grown by molecular beam epitaxy. Journal of Applied Physics, 2013, 113, 033501.	1.1	9
33	Threading dislocation propagation in AlGaN/GaN based HEMT structures grown on Si (111) by plasma assisted molecular beam epitaxy. Journal of Crystal Growth, 2012, 357, 35-41.	0.7	18
34	Si and Ge nanostructures epitaxy on a crystalline insulating LaAlO₃(001) substrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 657-662.	0.8	4
35	Strain relief: Mainspring of Ge semiconducting nanostructures growth on LaAlO3(001). Acta Materialia, 2012, 60, 1929-1936.	3.8	3
36	Cubic and hexagonal InGaAsN dilute arsenides by unintentional homogeneous incorporation of As into InGaN. Scripta Materialia, 2012, 66, 351-354.	2.6	1

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37	High-Resolution Electron Microscopy of Semiconductor Heterostructures and Nanostructures. Springer Series in Materials Science, 2012, , 23-62.	0.4	2
38	Fabrication of Barbed-Shaped SnO@SnO₂ Core/Shell Nanowires. Journal of Physical Chemistry C, 2011, 115, 4495-4501.	1.5	9
39	Improved Structural and Chemical Properties of Nearly Lattice-Matched Ternary and Quaternary Barriers for GaN-Based HEMTs. Crystal Growth and Design, 2011, 11, 2588-2591.	1.4	14
40	Influence of substrate crystallography on the room temperature synthesis of AlN thin films by reactive sputtering. Applied Surface Science, 2011, 257, 9306-9313.	3.1	16
41	Evaluation of the In desorption during the capping process of diluted nitride In(Ga)As quantum dots. Journal of Physics: Conference Series, 2011, 326, 012049.	0.3	0
42	Growth and characterization of InAlN layers nearly latticeâ€matched to GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2500-2502.	0.8	4
43	Growth mechanism and electronic properties of epitaxial In2O3films on sapphire. Journal of Applied Physics, 2011, 110, 093712.	1.1	22
44	Structural and compositional homogeneity of InAlN epitaxial layers nearly lattice-matched to GaN. Acta Materialia, 2010, 58, 4120-4125.	3.8	26
45	Natural oxidation of InN quantum dots: the role of cubic InN. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 9-12.	0.8	1
46	Phase mapping of aging process in InN nanostructures: oxygen incorporation and the role of the zinc blende phase. Nanotechnology, 2010, 21, 185706.	1.3	5
47	Atomic scale high-angle annular dark field STEM analysis of the N configuration in dilute nitrides of GaAs. Physical Review B, 2009, 80, .	1.1	22
48	Microstructural improvements of InP on GaAs (001) grown by molecular beam epitaxy by in situ hydrogenation and postgrowth annealing. Applied Physics Letters, 2009, 94, 041919.	1.5	10
49	Determination of the composition of InxGa1â^'xN from strain measurements. Acta Materialia, 2009, 57, 5681-5692.	3.8	65
50	Structural changes during the natural aging process of InN quantum dots. Journal of Applied Physics, 2009, 105, 013527.	1.1	8
51	Structure of cubic polytype indium nitride layers on top of modified sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 514-517.	0.8	4
52	Maghemiteâ€“silica nanocomposites: solâ€“gel processing enhancement of the magneto-optical response. Nanotechnology, 2008, 19, 475706.	1.3	16
53	High Resolution HAADF-STEM Imaging Analysis of N related defects in GaNAs Quantum Wells. Microscopy and Microanalysis, 2008, 14, 318-319.	0.2	4
54	Influence of the Growth Temperature on the Composition Fluctuations of GaInNAs/GaAs Quantum Wells. , 2008, , 199-221.		0

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55	Cubic InN growth on sapphire (0001) using cubic indium oxide as buffer layer. Applied Physics Letters, 2007, 90, 091901.	1.5	37
56	Configuration of the misfit dislocation networks in uncapped and capped InN quantum dots. Applied Physics Letters, 2007, 91, 071915.	1.5	12
57	Critical strain region evaluation of self-assembled semiconductor quantum dots. Nanotechnology, 2007, 18, 475503.	1.3	19
58	Strain Mapping at the Atomic Scale in Highly Mismatched Heterointerfaces. Advanced Functional Materials, 2007, 17, 2588-2593.	7.8	12
59	Kinetic considerations on the phase separation of GaInNAs quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1477-1480.	0.8	0
60	Evaluation of the influence of GaN and AlN as pseudosubstrates on the crystalline quality of InN layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1454-1457.	0.8	1
61	Strain Relief Analysis of InN Quantum Dots Grown on GaN. Nanoscale Research Letters, 2007, 2, 442-6.	3.1	14
62	Misfit relaxation of InN quantum dots: Effect of the GaN capping layer. Applied Physics Letters, 2006, 88, 151913.	1.5	35
63	Effect of the Growth Temperature in the Composition Fluctuation of GaInNAs/GaAs Quantum Wells. Microscopy and Microanalysis, 2006, 12, 754-755.	0.2	0
64	Structural characterization of InN quantum dots grown by Metalorganic Vapour Phase Epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1687-1690.	0.8	8
65	Effect of growth temperature on AlGaInN layers: a TEM analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1400-1403.	0.8	0
66	Role of elastic anisotropy in the vertical alignment of In(Ga)As quantum dot superlattices. Applied Physics Letters, 2006, 88, 193118.	1.5	18
67	Influence of structure and defects on the performance of dot-in-well laser structures. , 2005, , .		1
68	Effect of the growth parameters on the structure and morphology of InAs/InGaAs/GaAs DWELL quantum dot structures. Journal of Crystal Growth, 2005, 278, 151-155.	0.7	11
69	Strain interactions and defect formation in stacked InGaAs quantum dot and dot-in-well structures. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 245-251.	1.3	10
70	Structural and optical properties of high In and N content GaInNAs quantum wells. Thin Solid Films, 2005, 483, 185-190.	0.8	6
71	Critical barrier thickness for the formation of InGaAs/GaAs quantum dots. Materials Science and Engineering C, 2005, 25, 798-803.	3.8	5
72	Characterization of structure and defects in dot-in-well laser structures. Materials Science and Engineering C, 2005, 25, 793-797.	3.8	1

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73	Spinodal decomposition in GaInNAs/GaAs multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1292-1297.	0.8	0
74	Composition modulation in GaInNAs quantum wells: Comparison of experiment and theory. Journal of Applied Physics, 2005, 97, 073705.	1.1	14
75	Nucleation of InN quantum dots on GaN by metalorganic vapor phase epitaxy. Applied Physics Letters, 2005, 87, 263104.	1.5	28
76	An approach to the formation mechanism of the composition fluctuation in GaInNAs quantum wells. Semiconductor Science and Technology, 2005, 20, 1096-1102.	1.0	5
77	Unfaulting of dislocation loops in the GaInNAs alloy: An estimation of the stacking fault energy. Journal of Applied Physics, 2005, 98, 023521.	1.1	6
78	Carbon fiber reinforced polymers (CFRP) Nd:YAG laser machining. , 2004, , .		2
79	Influence of growth temperature on the structural and optical quality of GaInNAs/GaAs multi-quantum wells. Semiconductor Science and Technology, 2004, 19, 813-818.	1.0	20
80	Structural defects characterisation of GaInNAs MQWs by TEM and PL. IEE Proceedings: Optoelectronics, 2004, 151, 385-388.	0.8	3
81	Composition fluctuations in GaInNAs multi-quantum wells. IEE Proceedings: Optoelectronics, 2004, 151, 271-274.	0.8	0
82	Improvement in the optical quality of GaInNAs/GaInAs quantum well structures by interfacial strain reduction. IEE Proceedings: Optoelectronics, 2004, 151, 301-304.	0.8	2
83	Composition Modulation in Low Temperature Growth of InGaAs/GaAs System: Influence on Plastic Relaxation. Mikrochimica Acta, 2004, 145, 63-66.	2.5	2
84	Structural Study of Micro and Nanotubes Synthesized by Rapid Thermal Chemical Vapor Deposition. Mikrochimica Acta, 2004, 145, 129-132.	2.5	4
85	Microchemical Analysis and Microstructural Development of Cr-Doped Mullites. Mikrochimica Acta, 2004, 145, 255-260.	2.5	5
86	The role of Ge predeposition temperature in the MBE epitaxy of SiC on Ssilicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 341-346.	0.8	10
87	Size self-filtering effect in vertical stacks of InAs/InP self-assembled quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 174-176.	1.3	3
88	Transmission electron microscopy study of simultaneous high-dose C++N+ co-implantation into (111)Si. Thin Solid Films, 2003, 426, 16-30.	0.8	3
89	Fatigue behaviour of laser machined 2024 T3 aeronautic aluminium alloy. Applied Surface Science, 2003, 208-209, 194-198.	3.1	35
90	Microstructural study of CO2 laser machined heat affected zone of 2024 aluminum alloy. Applied Surface Science, 2003, 208-209, 210-217.	3.1	58

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91	SiC voids, mosaic microstructure and dislocations distribution in Si carbonized layers. Diamond and Related Materials, 2003, 12, 1227-1230.	1.8	18
92	Strain relaxation behavior of InxGa1â^'xAs quantum wells on vicinal GaAs (111)B substrates. Applied Physics Letters, 2002, 80, 1541-1543.	1.5	7
93	Correlation Between the AlN Buffer Layer Thickness and the GaN Polarity in GaN/AlN/Si(111) Grown by MBE. Materials Research Society Symposia Proceedings, 2002, 743, L3.25.1.	0.1	0
94	Size-filtering effects by stacking InAs/InP (001) self-assembled quantum wires into multilayers. Physical Review B, 2002, 65, .	1.1	25
95	Origin of Inversion Domains in GaN/AlN/Si(111) Heterostructures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 234, 935-938.	0.7	4
96	AlN buffer layer thickness influence on inversion domains in GaN/AlN/Si(111). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 181-184.	1.7	8
97	Relaxation study of AlGaAs cladding layers in InGaAs/GaAs (111)B lasers designed for 1.0â€“1.1Î¼m operation. Microelectronics Journal, 2002, 33, 553-557.	1.1	2
98	The role of climb and glide in misfit relief of InGaAs/GaAs(111)B heterostructures. Microelectronics Journal, 2002, 33, 559-563.	1.1	0
99	Effect of graded buffer design on the defect structure in InGaAs/GaAs (111)B heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 27-31.	1.7	5
100	Proton-induced damage in p+â€“n InP solar cells: the role of electron capture at high fluences. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 294-298.	1.7	1
101	Flame Spray Pyrolysis of Precursors as a Route to Nanoâ€mullite Powder: Powder Characterization and Sintering Behavior. Journal of the American Ceramic Society, 2001, 84, 951-961.	1.9	69
102	A mechanism for the multiple atomic configurations of inversion domain boundaries in GaN layers grown on Si(111). Applied Physics Letters, 2001, 79, 3588-3590.	1.5	13
103	Electron beam induced current and cathodoluminescence study of proton irradiated InAsxP1â^'x/InP quantum-well solar cells. Journal of Applied Physics, 2001, 90, 2840-2846.	1.1	14
104	Effect of indium content on the normal-incident photoresponse of InGaAs/GaAs quantum-well infrared photodetectors. Applied Physics Letters, 2001, 78, 2390-2392.	1.5	6
105	Radiation response ofn-type base InP solar cells. Journal of Applied Physics, 2001, 90, 3558-3565.	1.1	12
106	Inversion domains in GaN layers grown on (111) silicon by molecular-beam epitaxy. Applied Physics Letters, 2001, 78, 2688-2690.	1.5	12
107	Control of phase modulation in InGaAs epilayers. Applied Physics Letters, 2000, 76, 3236-3238.	1.5	8
108	Influence of buffer-layer surface morphology on the self-organized growth of InAs on InP(001) nanostructures. Applied Physics Letters, 2000, 76, 1104-1106.	1.5	133

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109	Radiation-induced orderâ€“disorder transition in p+â€“n InGaP solar cells. Applied Physics Letters, 1999, 74, 2684-2686.	1.5	8
110	The effect of Si doping on the defect structure of GaN/AlN/Si(111). Applied Physics Letters, 1999, 74, 3362-3364.	1.5	55
111	Spatial distribution of radiation-induced defects in p+-n InGaP solar cells. Applied Physics Letters, 1999, 74, 3812-3814.	1.5	7
112	Detailed defect study in proton irradiated InP/Si solar cells. Journal of Applied Physics, 1999, 86, 3584-3589.	1.1	9
113	Influence of substrate misorientation on the optical and structural properties of InGaAs/GaAs single strained quantum wells grown on (111)B GaAs by molecular beam epitaxy. Microelectronics Journal, 1999, 30, 373-378.	1.1	1
114	Piezoelectric InGaAs/GaAs (111)B multiple quantum well photodiodes: optoelectronic properties by electron beam induced current and cathodoluminescence. Microelectronics Journal, 1999, 30, 413-417.	1.1	6
115	Cathodoluminescence study of pyramidal facets in piezoelectric InGaAs/GaAs multiple quantum well pin photodiodes. Microelectronics Journal, 1999, 30, 427-431.	1.1	3
116	Multiple quantum well GaAs/AlGaAs solar cells: transport and recombination properties by means of EBIC and cathodoluminescence. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 66, 151-156.	1.7	8
117	Failure analysis of heavily proton irradiated p+-n InGaP solar cells by EBIC and cathodoluminescence. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 66, 189-193.	1.7	0
118	Transmission electron microscopy study of InGaAs/InP superlattices grown on V-shaped surface InP substrates. Applied Surface Science, 1999, 144-145, 488-491.	3.1	0
119	New relaxation mechanisms in InGaAs/GaAs (111) multiple quantum well. Microelectronics Journal, 1999, 30, 467-470.	1.1	4
120	Growth of III-nitrides on Si(111) by molecular beam epitaxy Doping, optical, and electrical properties. Journal of Crystal Growth, 1999, 201-202, 296-317.	0.7	189
121	MBE growth of GaN and AlGaN layers on Si(111) substrates: doping effects. Journal of Crystal Growth, 1999, 201-202, 415-418.	0.7	20
122	Optical properties of InxGa1â^'xAs/GaAs MQW structures on (111)B GaAs grown by MBE: dependence on substrate miscut. Journal of Crystal Growth, 1999, 201-202, 1085-1088.	0.7	3
123	Relaxation study of InxGa1â^'xAs/GaAs quantum-well structures grown by MBE on (001) and (111)B GaAs for long wavelength applications. Journal of Crystal Growth, 1999, 206, 287-293.	0.7	4
124	Effect of In-content on the misfit dislocation interaction in InGaAs/GaAs layers. Thin Solid Films, 1999, 343-344, 302-304.	0.8	0
125	Electron microscopy study of SiC obtained by the carbonization of Si(111). Thin Solid Films, 1999, 343-344, 305-308.	0.8	11
126	Influence of substrate misorientation on the structural characteristics of InGaAs/GaAs MQW on (111)B GaAs grown by MBE. Thin Solid Films, 1999, 343-344, 558-561.	0.8	3

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127	Influence of Si Doping on the Subgrain Structure of GaN Grown on AlN/Si(111). Physica Status Solidi A, 1999, 176, 401-406.	1.7	5
128	Growth rate and critical temperatures to avoid the modulation of composition of InGaAs epitaxial layers. Applied Physics Letters, 1999, 74, 2649-2651.	1.5	11
129	Critical thickness for the saturation state of strain relaxation in the InGaAs/GaAs systems. Applied Physics Letters, 1998, 72, 1875-1877.	1.5	11
130	Optical emission of a one-dimensional electron gas in semiconductor V-shaped quantum wires. Physical Review B, 1998, 58, 10705-10708.	1.1	0
131	Characterisation by TEM and X-ray diffraction of linearly graded composition InGaAs buffer layers on (001) GaAs. Materials Science and Technology, 1998, 14, 1273-1278.	0.8	0
132	Work-hardening effects in the lattice relaxation of single layer heterostructures. Applied Physics Letters, 1997, 71, 2475-2477.	1.5	10
133	A work-hardening based model of the strain relief in multilayer graded-buffer structures. Applied Physics Letters, 1997, 71, 3099-3101.	1.5	11
134	Structural study of AlGaAs/InGaAs superlattices grown by MBE on (111)B GaAs substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 106-109.	1.7	1
135	EBIC mode characterization of transport properties on laser heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 57-60.	1.7	2
136	Advantages of thin interfaces in step-graded buffer structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 41-45.	1.7	1
137	Comparison of the crystalline quality of step-graded and continuously graded InGaAs buffer layers. Journal of Crystal Growth, 1996, 169, 649-659.	0.7	44
138	Energy-loss dependence of inelastic interactions between high-energy electrons and semiconductors: a model to determine the spatial distribution of electron-hole pairs generation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 168-171.	1.7	2
139	SCH laser recombination rate from EBIC profiles. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 172-175.	1.7	6
140	Design of InGaAs linear graded buffer structures. Applied Physics Letters, 1995, 66, 3334-3336.	1.5	70
141	Dislocation behavior in InGaAs stepâ€•and alternating stepâ€graded structures: Design rules for buffer fabrication. Applied Physics Letters, 1995, 67, 3632-3634.	1.5	18
142	Strain relief in linearly graded composition buffer layers: A design scheme to grow dislocationâ€free (<105cmâ^'2) and unstrained epilayers. Applied Physics Letters, 1994, 65, 2460-2462.	1.5	47
143	A study of the defect structure in GaAs layers grown at low and high temperatures on Si(001) substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 196-199.	1.7	1
144	Step-graded buffer layer study of the strain relaxation by transmission electron microscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 497-501.	1.7	10

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145	Transmission electron microscopy study of multilayer buffer structures used as dislocation filters. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 515-519.	1.7	1
146	A comparative study of Coî—¸Re superlattices sputtered on glass and Si substrates by grazing angle of incidence RBS, HRTEM, PAC, magnetic and transport properties studies. Nuclear Instruments & Methods in Physics Research B, 1994, 85, 202-205.	0.6	6
147	A study of the evolution process of antiphase boundaries in GaAs on Si. Journal of Electronic Materials, 1993, 22, 567-572.	1.0	9
148	Dislocation Distribution in Graded Composition IngaAs Layers. Materials Research Society Symposia Proceedings, 1993, 325, 223.	0.1	3
149	Experimental evidence of the structure of annihilation of antiphase boundaries in GaAs on Si. Materials Letters, 1993, 15, 353-355.	1.3	0
150	Tem Characterization of GaAs Pin Diodes at Low Temperatures on Si Substrates. Materials Research Society Symposia Proceedings, 1993, 326, 97.	0.1	0
151	Structural Characterization of GaP/GaAs/GaP Heterostructure by TEM. Materials Research Society Symposia Proceedings, 1992, 280, 449.	0.1	0
152	High-resolution electron microscopy study of ALMBE InAs grown on (001) GaAs substrates. Ultramicroscopy, 1992, 40, 370-375.	0.8	1
153	HREM characterization of metal catalysts supported on rare-earth oxides: samarium oxide as support. Ultramicroscopy, 1990, 34, 60-65.	0.8	18
154	Metal-Support Interaction Phenomena in Some High Metal Loading Lanthana Supported Rhodium Catalysts. Studies in Surface Science and Catalysis, 1989, , 123-132.	1.5	10
155	Electron Microscopy study of metal-support interaction in Rh/CeO₂ catalysts. Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 256-257.	0.0	1
156	Study of the interaction of two hexagonal neodymium oxides with atmospheric CO2 and H2O. Journal of Materials Science, 1988, 23, 1474-1480.	1.7	9
157	Characterisation of rare earth oxide supported metal catalysts. Study of some ceria supported rhodium phases. Catalysis Today, 1988, 2, 653-662.	2.2	43
158	The chemistry in air of the rare-earth-metal sesquioxides. Comparative study of hexagonal and cubic neodymia samples. Journal of the Chemical Society Dalton Transactions, 1988, , 1765-1771.	1.1	7
159	Behaviour of rare earth sesquioxides exposed to atmospheric carbon dioxide and water. Reactivity of Solids, 1987, 4, 23-40.	0.3	129
160	Preparation of lanthana supported rhodium catalysts. Occurrence of heavy carbonation phenomena on the support.. Applied Catalysis, 1987, 31, 267-273.	1.1	22
161	The influence of the structural nature of samaria on its behaviour against atmospheric CO2 and H2O. Materials Letters, 1987, 6, 71-74.	1.3	3
162	Study of the support evolution through the process of preparation of rhodium/lanthana catalysts. Journal of the Chemical Society Faraday Transactions I, 1987, 83, 2279.	1.0	13

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163	Solid state chemistry of the preparation of lanthana-supported metal catalysts ? study of the impregnation step. Journal of Materials Science, 1987, 22, 3793-3800.	1.7	19
164	Behaviour of neodymia as a support of highly dispersed rhodium. Inorganica Chimica Acta, 1987, 140, 49-51.	1.2	1
165	Stem and microdiffraction studies of Rh/CeO2. Micron and Microscopica Acta, 1987, 18, 165-169.	0.2	25
166	Preparation of some rare earth oxide supported rhodium catalysts: Study of the supports. Materials Chemistry and Physics, 1987, 17, 433-443.	2.0	7
167	Preparation of catalysts constituted by rhodium supported on two cerium dioxides with different surface area. Materials Chemistry and Physics, 1987, 18, 119-127.	2.0	19
168	Study of the aging in air of a cubic sample of samaria. Materials Research Bulletin, 1987, 22, 131-138.	2.7	10
169	Comments on the preparation of M/4f oxide catalysts. Applied Catalysis, 1986, 21, 379-382.	1.1	13
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